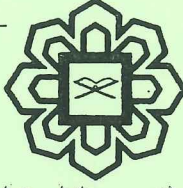


MODEL ANSWER

Name: _____

Matric No: _____ Section: _____



الجامعة الإسلامية العالمية ماليزيا

INTERNATIONAL ISLAMIC UNIVERSITY MALAYSIA

MID-TERM EXAMINATION
SEMESTER II, 2013/2014 SESSION
KULLIYAH OF ENGINEERING

Programme : ENGINEERING Level of Study : UG 2
Time : 8:00 pm-10:00 pm Date : 20/03/2014
Duration : 2 Hours
Course Code : ECE 2133 Section(s) : 1 & 2
Course Title : **Electronic Circuits**

This Question Paper consists of **Eight (8)** Printed Pages (Including Cover and a blank page) with **Three (3)** Questions.

INSTRUCTION(S) TO CANDIDATES

DO NOT OPEN UNTIL YOU ARE ASKED TO DO SO

- Use only pen for writing answer.
- Do not use your own sheet.
- A total mark of this examination is 60.
- This examination is worth 30% of the total assessment.
- For drawing you may use pencil
- Answer **ALL THREE(3)** questions.
- Answer on the question paper.

Any form of cheating or attempt to cheat is a serious offence which may lead to dismissal.

	Question 1	Question 2	Question 3	Total Marks
Marks	20	20	20	60
Marks Obtained				

Q.1 [20 marks]

- (a) Consider the circuit shown in Fig. 1(a), derive the expression (step by step) for the voltage transfer function $T(s) = \frac{v_o(s)}{v_i(s)}$ and find the time constant and the corner frequency. (8 marks)

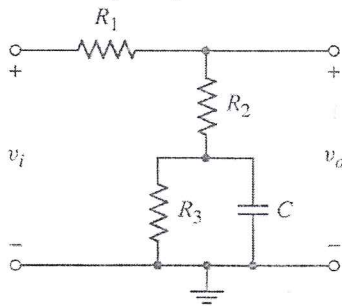


Fig. 1(a)

$$R_3 \parallel \frac{1}{sC} = \frac{R_3 \left(\frac{1}{sC} \right)}{R_3 + \frac{1}{sC}} = \frac{R_3}{1 + sR_3C}$$

$$T(s) = \frac{v_o(s)}{v_i(s)} = \frac{R_2 + \frac{R_3}{1 + sR_3C}}{R_1 + R_2 + \frac{R_3}{1 + sR_3C}}$$

$$= \frac{R_2 + R_3 + sR_2R_3C}{R_1 + R_2 + R_3 + s(R_1 + R_2)R_3C}$$

$$= \frac{R_2 + R_3}{R_1 + R_2 + R_3} \cdot \frac{\left[1 + \frac{sR_2R_3C}{(R_2 + R_3)} \right]}{\left[1 + \frac{s(R_1 + R_2)R_3C}{(R_1 + R_2) + R_3} \right]}$$

$$= K \cdot \frac{1 + s\tau_A}{1 + s\tau_B}$$

$$\tau_A = \frac{R_2R_3}{R_2 + R_3} C = (R_2 \parallel R_3) C$$

$$\tau_B = \frac{(R_1 + R_2)R_3}{(R_1 + R_2) + R_3} \cdot C = (R_1 + R_2) \parallel R_3 \cdot C$$

$$\therefore f_A = \frac{1}{2\pi\tau_A}$$

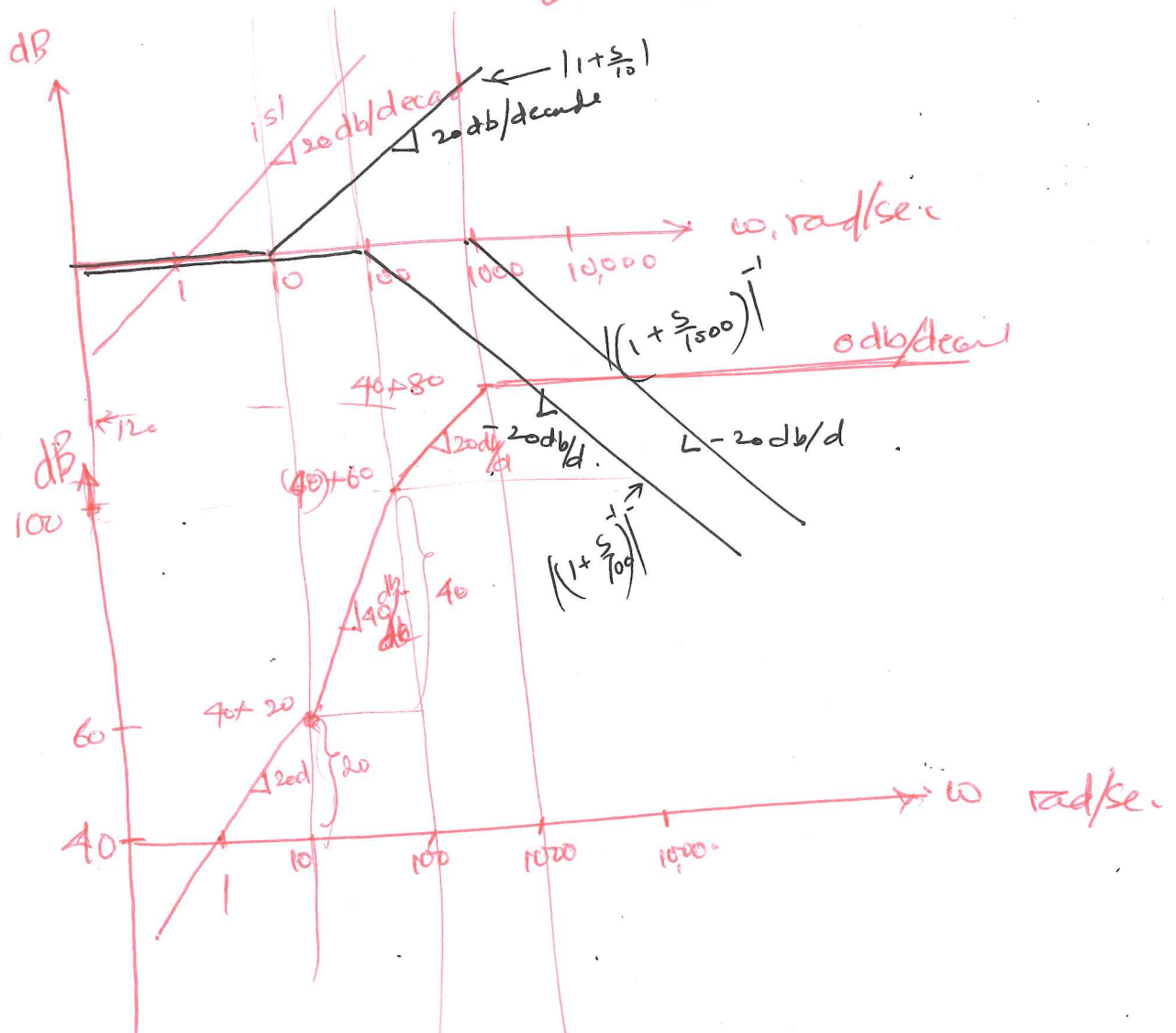
$$\therefore f_B = \frac{1}{2\pi\tau_B}$$

(b) Draw the Bode plot (magnitude and phase) of the following transfer function. (12 marks)

$$T(s) = \frac{10^6 s(s+10)}{(s+100)(s+1000)}$$

$$= \frac{10^6 \cdot s \times 10 \left[1 + \frac{s}{10}\right]}{100 \left[1 + \frac{s}{100}\right] 1000 \left[1 + \frac{s}{1000}\right]}$$

$$= \frac{100 s \cdot \left[1 + \frac{s}{10}\right]}{\left[1 + \frac{s}{100}\right] \left[1 + \frac{s}{1000}\right]}$$

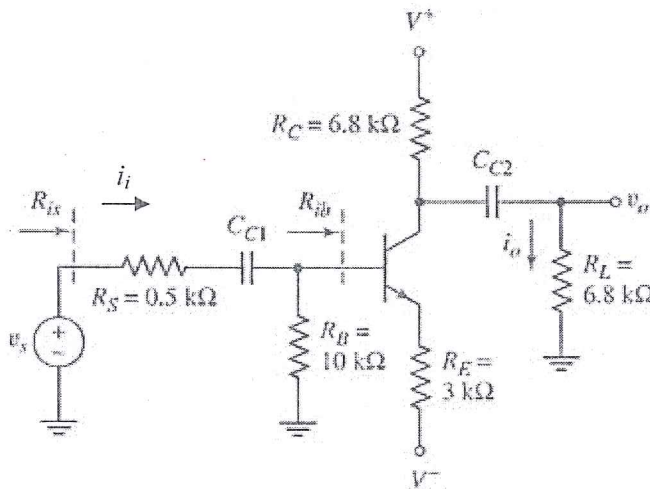


Q.2 [20 marks]

(a) Draw the small signal equivalent circuit diagram of the circuit shown in Fig. 2(a) and find the followings: (10 marks)

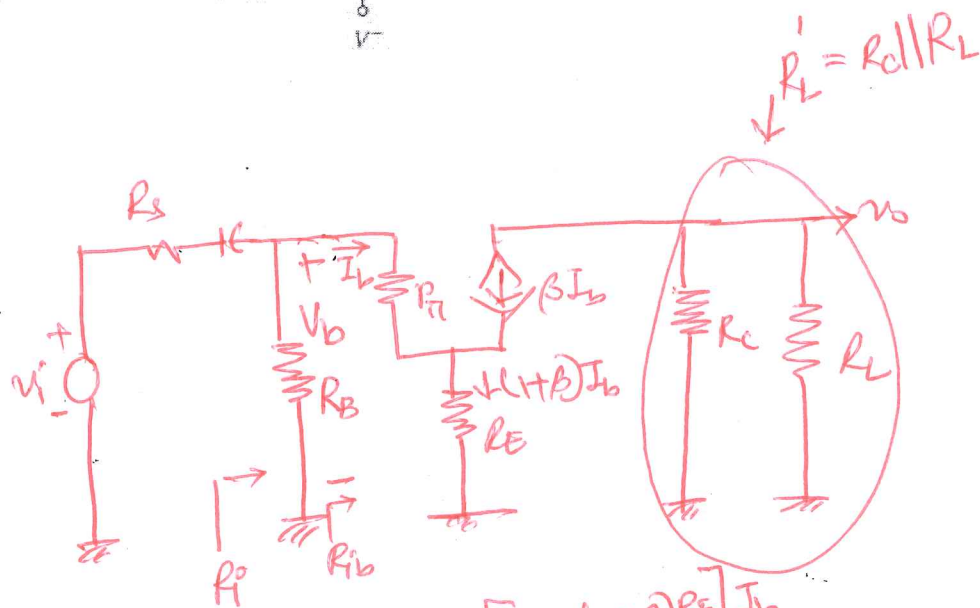
Find the small signal midband voltage gain $A_v = \frac{v_o}{v_s}$ and the lower corner frequency due to C_{C1} assuming that $C_{C2} = \infty$.

Given that ~~$R_s = 0.5 \text{ k}\Omega$, $R_1 = 330 \text{ k}\Omega$, $R_2 = 85 \text{ k}\Omega$, $R_C = 4 \text{ k}\Omega$, $R_E = 1.5 \text{ k}\Omega$, $C_{C1} = 1 \mu\text{F}$ and $C_{C2} = \infty$. The transistor has small-signal hybrid- π parameters, $r_{\pi} = 3 \text{ k}\Omega$, $g_m = 40 \text{ mA/V}$ and $r_o = \infty$.~~



$\beta = g_m r_{\pi}$
 $= 40 \times 3 = 120$

Fig. 2(a)



$V_b = r_{\pi} I_b + (1 + \beta) I_b R_E = [r_{\pi} + (1 + \beta) R_E] I_b$

$v_o = -\beta I_b R'_L$

$R_{ib} = \frac{V_b}{I_b} = r_{\pi} + (1 + \beta) R_E$

$A_{v_A} = \frac{v_o}{v_b} = \frac{-\beta I_b R'_L}{[r_{\pi} + (1 + \beta) R_E] I_b}$

$= 3 + (1 + 120) \times 3$
 $= 366 \text{ k}$

$= \frac{-\beta R'_L}{r_{\pi} + (1 + \beta) R_E}$
 $= \frac{-120 \times 3.4}{366} = -1.11474$

$R'_L = 6.8 || 6.8 = 3.4 \text{ k}$

$$R_i = R_{cb} \parallel R_B$$
$$= 366 \parallel 10 = 9.73 \text{ k}$$

$$\therefore A_v = A_{vA} \frac{R_i}{R_i + R_s} = -1.1147 \times \frac{9.73}{9.73 + 0.5}$$
$$= -1.06 \text{ V/V} \quad \leftarrow$$

$$\tau = (R_s + R_i) C_{c1} = (0.5 + 9.73) \times 1 \mu$$
$$= 10.23 \text{ ms}$$

$$\therefore f_L = \frac{1}{2\pi\tau} = 15.55 \text{ Hz} \quad \leftarrow$$

(b) Draw the small signal equivalent circuit diagram of the circuit shown in Fig. 2(b) and find the followings: (10 marks)

- (i) the midband voltage gain $A_v = \frac{v_o}{v_i}$,
- (ii) the output resistance R_o of the amplifier, and
- (iii) the corner frequency due to $C_L = 4$ pF assumed that $C_C \rightarrow \infty$.

Given that $R_{Si} = 1$ k Ω , $R_1 = 180$ k Ω , $R_2 = 330$ k Ω , $R_S = 3.0$ k Ω , $R_L = 6$ k Ω . The transistor parameters are $g_m = 0.65$ mA/V and $r_o = 100$ k Ω .

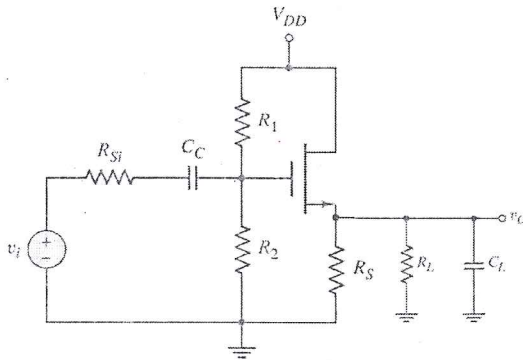
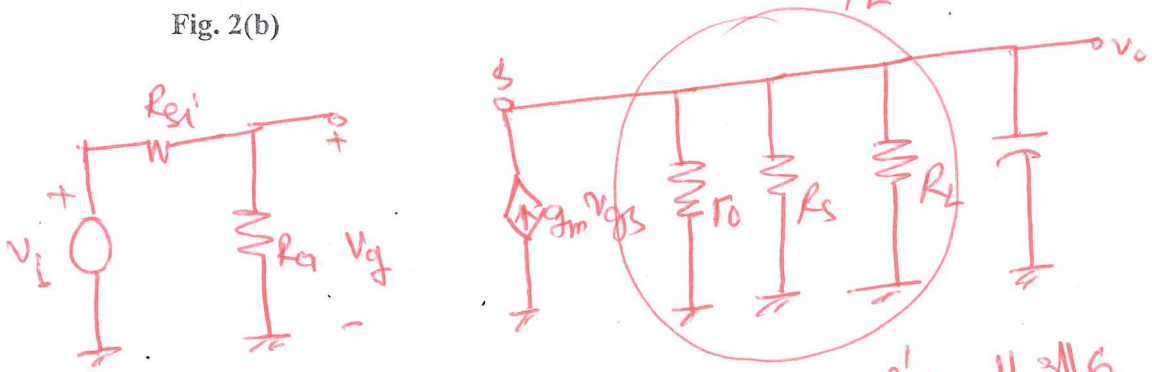
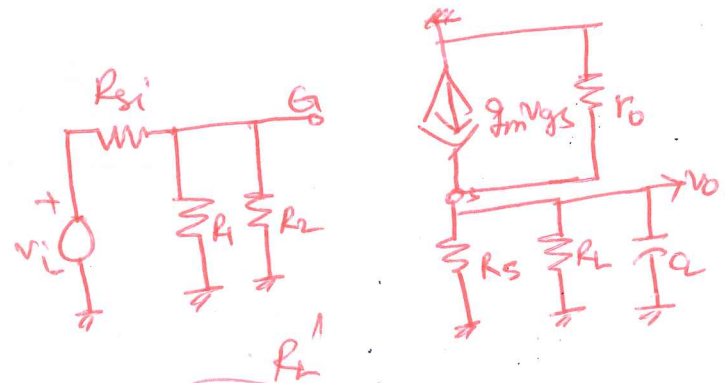


Fig. 2(b)



$$R_L' = 100 \parallel 3 \parallel 6 = 1.961 \text{ k}\Omega$$

(1) Midband gain

$$v_o = g_m v_{gs} R_L'$$

$$v_{gs} = v_{gs} + g_m v_{gs} R_L'$$

$$= v_{gs} (1 + g_m R_L')$$

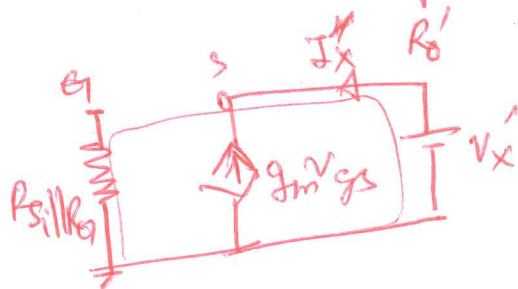
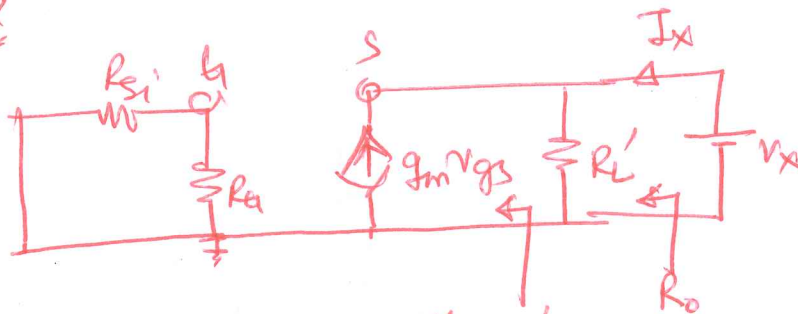
$$A_{VA} = \frac{v_o}{v_{gs}} = \frac{g_m R_L'}{1 + g_m R_L'} = \frac{0.65 \times 1.961}{1 + 0.65 \times 1.961} = 0.560 \text{ V/V}$$

$$R_{eq} = R_1 \parallel R_2 = 180 \parallel 330 = 116.47 \text{ k}\Omega$$

$$A_v = A_{vA} \times \frac{R_o}{R_{si} + R_i} = 0.56 \times \frac{116.47}{1 + 116.47}$$

$$= 0.555 \text{ V/V. } \leftarrow$$

ii) $R_o = ?$



$$I_x' = -g_m v_{gs}$$

$$v_{gs} + v_x' = 0$$

$$\therefore v_x' = -v_{gs}$$

$$\therefore I_x' = g_m v_x' \quad \therefore R_o' = \frac{v_x'}{I_x'} = \frac{1}{g_m}$$

$$\therefore R_o = R_o' \parallel R_d' = \left(\frac{1}{0.65} \right) \parallel 1.961 = 862.11 \Omega \quad \leftarrow$$

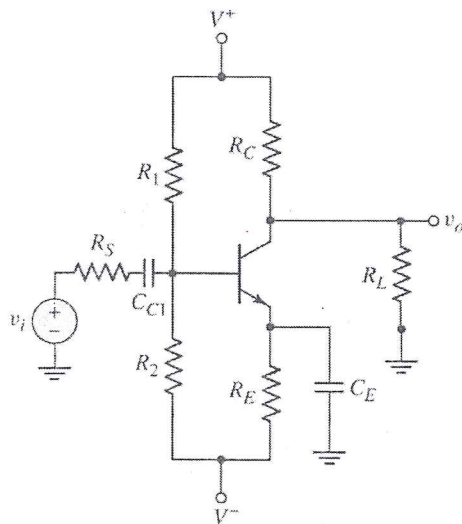
(iii) $\tau = C_L \times R_o = 4p \times 862.11 = 3.448 \text{ ns}$

$$\therefore f_H = \frac{1}{2\pi\tau} = 46.15 \text{ MHz } \leftarrow$$

(b) The common emitter amplifier is shown in Fig. 3(b) and operated at high frequencies. Draw the simplified high-frequency small signal equivalent circuit diagram and

(i) find the Miller capacitance, and

(ii) determine the upper 3dB frequency (f_H) considering Miller capacitance and without considering Miller capacitance. (10 marks)



The circuit parameters are:

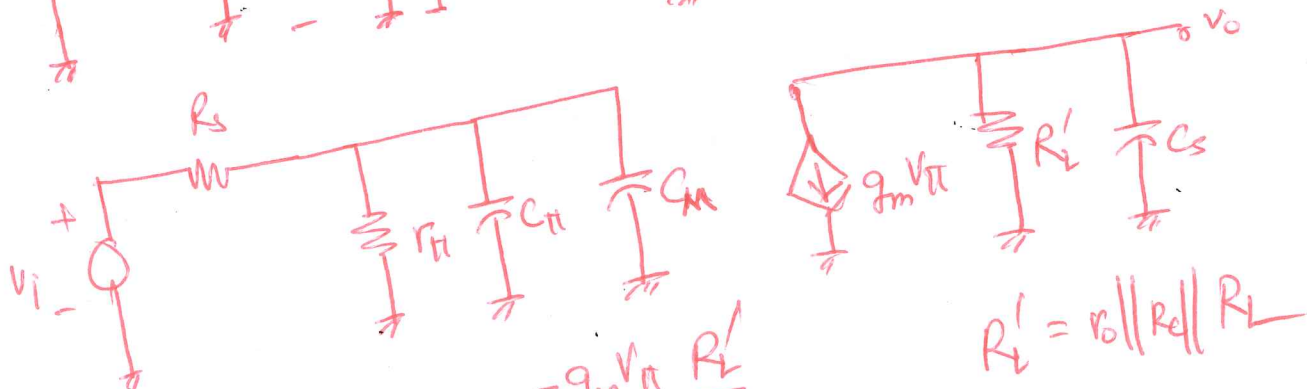
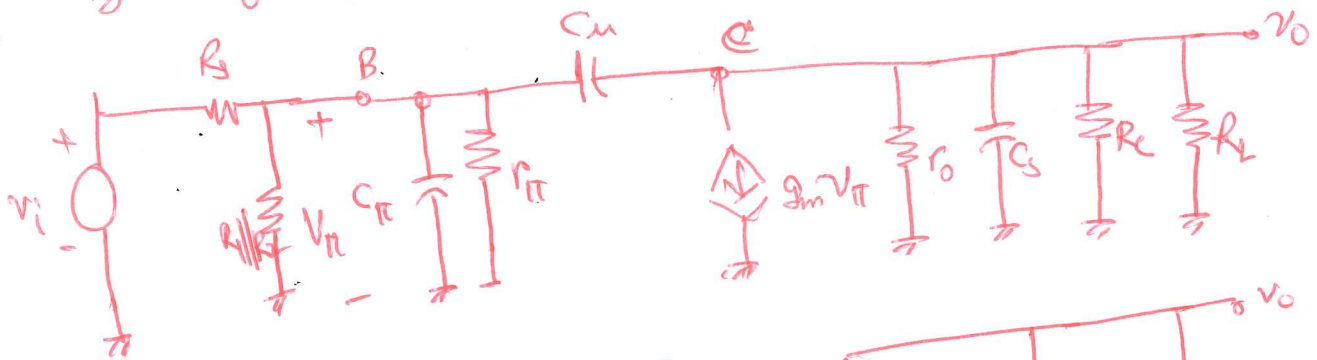
$R_S=1\text{k}\Omega$, $R_1=120\text{k}\Omega$, $R_2=20\text{k}\Omega$, $R_E=2\text{k}\Omega$, $R_C=5\text{k}\Omega$, $R_L=20\text{k}\Omega$, $C_{C1}=\infty$ and $C_E=\infty$.

The transistor parameters are :

$r_\pi = 3\text{k}\Omega$, $g_m = 40\text{ mA/V}$ and $r_o = 100\text{k}\Omega$, $C_\pi = 25\text{ pF}$, and $C_\mu = 4\text{ pF}$

Fig. 3(b)

** High frequency equivalent circuit diagram*



$$A_{vA} = \frac{v_o}{v_i} = \frac{-g_m V_\pi R'_L}{V_\pi}$$

$$= -g_m R'_L$$

$$= -40 \times (100 \parallel 5 \parallel 20) = -153.846$$

$$i) C_M = C_u [1 - A_v] \\ = 4p [1 + 153.846]k = 619.384pF$$

$$ii) \tau_{wo} = C_{eq} R_{eq}$$

$$R_{eq} = (R_s \parallel R_1 \parallel R_2 \parallel R_f)$$

$$= 1 \parallel 120 \parallel 20 \parallel 3$$

$$= 718.563 \Omega$$

with Miller Capacitance

$$C_T = C_u + C_M \\ = 25p + 619.384p \\ = 644.384p$$

$$\tau_m = 463.03 ns$$

$$f_{HM} = \frac{1}{2\pi \tau_m} = 343.724 kHz \leftarrow$$

with out Miller Capacitance

$$C_T = C_u = 25p$$

$$\therefore \tau_{wo} = 17.96 ns$$

$$\therefore f_{Hwo} = 8.859 MHz \leftarrow$$

Q.3 [20 marks]

(a) Draw the simplified high frequency small-signal equivalent circuit diagram of the ac circuit shown in Fig. 3(a) and derive step by step short circuit current gain $A_i = I_d/I_g$. Then find cutoff frequency f_T . (10 marks)

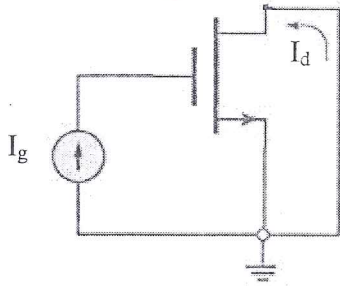
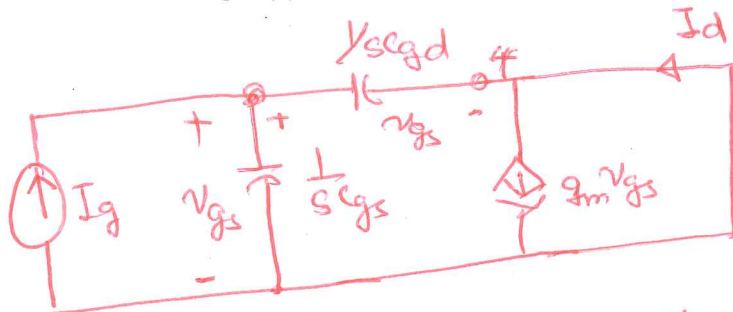
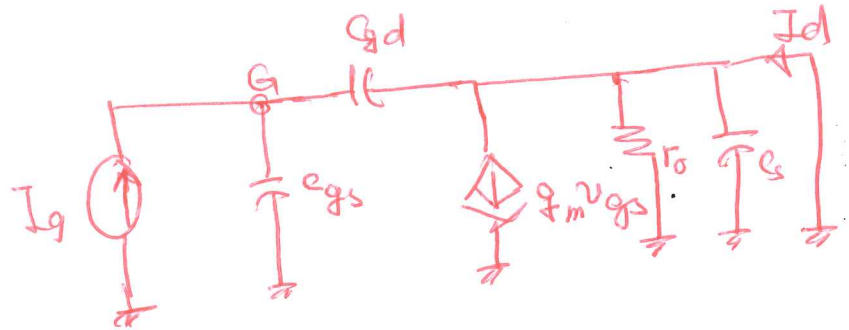


Fig. 3(a)



$$I_d = g_m v_{gs} - \frac{v_{gs}}{1/sC_{gd}} = v_{gs} [g_m - sC_{gd}]$$

$$I_g = \frac{v_{gs}}{1/sC_{gs}} + \frac{v_{gs}}{1/sC_{gd}} = v_{gs} [sC_{gs} + sC_{gd}]$$

$$\therefore A_i = \frac{I_d}{I_g} = \frac{g_m - sC_{gd}}{s(C_{gs} + C_{gd})} \approx \frac{g_m}{s(C_{gs} + C_{gd})}$$

considering $(g_m \gg sC_{gd})$
($s = j\omega$)

$$|A_i| = \left| \frac{g_m}{s(C_{gs} + C_{gd})} \right| = \frac{g_m}{\omega(C_{gs} + C_{gd})}$$

For cut off freq $|A_i| = 1 = \frac{g_m}{\omega_T (C_{gs} + C_{gd})}$

$$\therefore \omega_T = \frac{g_m}{(C_{gs} + C_{gd})} \text{ rad/sec} \quad f_T = \frac{g_m}{2\pi (C_{gs} + C_{gd})}$$